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selectively forming a first interconnect in the first contact hole and on prescribed area of the first interlayer insulating film so as to be electrically connected to [the integrated circuit and] the capacitor;

forming a second interlayer insulating layer, the entire part of the second interlayer insulating layer [~~is formed by thermal ozone TEOS~~] have a tensile stress so as to cover the first interconnect;

~~[subjecting the first interconnect to a first thermal treatment;]~~

forming a second contact hole in the second interlayer insulating film;

selectively forming a second interconnect in the second contact hole and on a prescribed area of the second interlayer insulating [film] layer so as to be electrically connected to the first interconnect through a second contact hole;

~~— subjecting the second interconnect to a second thermal treatment; and~~

~~— forming a passivation later so as to cover the second interconnect].~~

47 The method for fabricating a semiconductor device according to claim 28, wherein the second interlayer insulating layer is thermal ozone TEOS.